

U.S. Department of Commerce, Patent and Trademark Office  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Application No.:	Unknown
		Filing Date:	Unknown
		First Named Inventor:	Hamza Yilmaz
		Group Art Unit:	Unknown
		Examiner Name:	Unknown
		Confirmation No.:	Unknown
Attorney Docket No.:	YMZ004 US		

U.S. Patent Documents							
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1.	5,168,331	12/01/92	Yilmaz	257	331	
	2.	5,216,275	06/01/93	Chen	257	493	
Foreign Patent Documents							
							Translation
		Document	Date	Country	Class	Subclass	Yes
Other Art (Including Author, Title, Date, Pertinent Pages, Etc.)							
	3.	Jongdae Kim et al., "High-Density Trench DMOSFETs Employing Two Step Trench Technique and Trench Contact Structure", ISPSD-2003 Proceedings, pp. 1-4					
	4.	Il-Yong Park et al., "Novel Process Techniques for Fabricating High Density Trench MOSFETs with Self-Aligned N <sup>+</sup> /P <sup>+</sup> Source Formed on the Trench Side Wall", ISPSD-2003 Proceedings, pp. 1-4.					
	5.	M.A.A. In 'tZandt, et al., "Record-low 4mΩ mm <sup>2</sup> specific on-resistance for 20V Trench MOSFETs", ISPSD-2003 Proceedings, pp. 1-4.					
	6.	Mohamed Darwish et al., "A New Power W-Gated Trench MOSFET (WMOSFET) with High Switching Performance", ISPSD-2003 Proceedings, pp 1-4.					
	7.	Syotaro Ono et al., "30V New Fine Trench MOSFET with Ultra Low On-Resistance", ISPSD-2003 Proceedings, pp. 1-4.					

Examiner:	Date Considered:
* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.	